NANOWIRES'15

BARCELONA, SPAIN, OCTOBER 26TH-30TH 2015

NANOWIRE GROWTH WORKSHOP
NANOWIRES WORKSHOP

congresses.icmab.es/nanowires2015

PROGRAM COMMITTEES:

Nanowires Growth Workshop:
Lutz Geelhaar **(Chair) (PDI Berlin, Germany)**

Nanowires:
Jordi Arbiol **(Chair) (ICREA & ICN2, Catalonia, Spain)**
Riccardo Rurali **(Chair) (ICMAB-CSIC, Catalonia, Spain)**

LOCAL ORGANIZING COMMITTEE:

Jordi Arbiol	**ICREA & ICN2**
María de la Mata	**ICN2**
Miquel Royo	**ICMAB-CSIC**
Riccardo Rurali	**ICMAB-CSIC**
Montse Salas	**ICMAB-CSIC – msalas@icmab.es**

Additional information:
http://www.icmab.es/NANOWIRES2015

SCIENTIFIC PROGRAM

Monday 26th October 2015

12:00 – 14:00	**REGISTRATION**
14:00 – 14:15	**OPENING CEREMONY** Riccardo Rurali / Jordi Arbiol

NANOWIRE GROWTH WORKSHOP

NGW: Growth Evolution

Session Chair: Lutz Geelhaar

14:15 – 14:45	**Miroslav Kolibal** VUT Brno, Czech Republic *Germanium Nanowire Growth in Scanning Electron Microscope* **Invited**
14:45 – 15:00	**Michael A. Filler** Georgia Institute of Technology, US *Sub-Eutectic Vapour-Liquid-Solid Growth of Ge Nanowires Enabled by Sidewall Hydrogen*
15:00 – 15:15	**Vladimir Kaganer** PDI, Germany *Coalescence of spontaneously formed GaN nanowires in plasma-assisted molecular beam epitaxy*
15:15 – 15:30	**Philipp Schroth** Universität Siegen & KIT, Germany *Polytypism in growing self-catalyzed GaAs nanowires probed by time resolved in-situ high-resolution X-ray diffraction*
15:30 – 15:45	**Daniel Jacobsson** Lund University, Sweden *Real time imaging of growing GaAs nanowires under transient growth conditions*

15:45 – 16:15	**COFFEE BREAK & EXHIBITION (HALL)**

NGW: Heterostructures

Session Chair: Erik Bakkers

16:15 – 16:45	**Moira Hocevar** Institut Néel, France *Si/III-V nanowire heterostructures* Invited
16:45 – 17:00	**Giacomo Priante** CNRS-Laboratoire de Photonique et de Nanostructures, France *GaP/GaAs Axial Heterostructures in Self-Catalyzed Nanowires*
17:00 – 17:15	**Valentina Zannier** NEST, Italy *Growth of GaAs/InAs and InAs/GaAs axial heterostructured nanowires by Chemical beam epitaxy*
17:15 – 17:30	**Edith Bellet-Amalric** Univ. Grenoble Alpes & CNRS, Institut NEEL & CEA, INAC-SP2M, France *Single-temperature growth of II-VI dots in core-shell nanowires*
17:30 – 17:45	**Diana Car** TU/e, Netherlands *Adding functionality: InSb nanowires with built-in tunnel barriers*
17:45 – 18:00	**Ryan B. Lewis** PDI, Germany *Elastic and plastic strain relaxation in GaAs/(In,Ga)As core-shell nanowire heterostructures*

Tuesday 27th October 2015

NGW: Basic Growth Mechanisms

Session Chair: Michael Filler

9:00 – 09:30	**Jianhua Zhao** Invited Chinese Academy of Sciences, China *Molecular-beam epitaxy of high-quality InAs/InSb heterostructure nanowires on Si(111)*
9:30 – 9:45	**Luna Namazi** Lund University, Sweden *Direct Nucleation, Morphology and Compositional Tuning of InAs1- xSbx Nanowires on InAs (111) B Substrates*
9:45 – 10:00	**Yury Berdnikov** St. Petersburg Academic University, Russia *Regimes of self-catalysed nanowires growth*
10:00 – 10:15	**Emmanouil Dimakis** Helmholtz-Zentrum Dresden-Rossendorf, Germany *New possibilities in the self-catalyzed growth of GaAs nanowires using a modification of migration-enhanced epitaxy*
10:15 – 10:30	**Frank Glas** CNRS - Laboratoire de Photonique et de Nanostructures, France *Critical examination of the mononucleation hypothesis and joint modelling of the kinetics and statistics of self-catalyzed NW growth*
10:30 – 11:15	**COFFEE BREAK & EXHIBITION (HALL)**

NGW: Advanced Structures

Session Chair: Kimberly Dick

11:15 – 11:30	**Robert Day** Harvard University, US *Plateau-Rayleigh Crystal Growth of Periodic Shells on Synthesized and Fabricated 1D Substrates*
11:30 – 11:45	**Lin Tian** IMM-CNR, Italy *Synthesis of Au- or In-seeded Si NWs on flexible organic substrates*

11:45 – 12:00	**Alexander Kelrich** Technion, Israel *Growth of InP nanoflags and planar nanowires by in situ catalyst manipulation*
12:00 – 12:15	**Bernhard Loitsch** WSI, TU München, Germany *Tunable quantum confinement in ultrathin GaAs based nanowires via reverse reaction growth*
12:15 – 12:30	**Torsten Rieger** Peter Grünberg Institute, Forschungszentrum Jülich GmbH, Germany *Self-assembled InAs nanowire junctions on Si substrates*

12:30 – 14:30	**LUNCH (included)**

NGW: Selective Area Growth

Session Chair: Hadas Shtrikman

14:30 – 14:45	**Mattias Borg** IBM Research – Zurich, Switzerland *Template-Assisted Selective Epitaxy: Highly controlled III-V nanowire integration on Si*
14:45 – 15:00	**Jelena Vukaljovic** EPFL, Switzerland *InAs Growth in Si/SiO2 Nanotubes by Molecular Beam Epitaxy*
15:00 – 15:15	**Dingding Ren** Norwegian University of Science and Technology (NTNU), Norway *High-yield Self-catalyzed GaAsSb/GaAs Heterostructured Nanowire Array on Si(111) by Molecular Beam Epitaxy*
15:15 – 15:30	**Vladimir Dubrovskii** Ioffe Physical technical Institute (RAS) & ITMO University, Russia *Narrowing the radius distribution of Ga-catalyzed GaAs nanowires*

15:30 – 17:30	**POSTER SESSION A (see page 11) & EXHIBITION (HALL)**

NGW: Polytypism

Session Chair: Isabel Alonso

17:30 – 18:00	**Evelyne Gil** Institut Pascal, France *VLS growth from chloride gaseous precursors: fast atomistic growth process for polytypism-free III-V NWs with record aspect ratio* **Invited**
18:00 – 18:15	**Simone Assali** TU/e, Netherlands *Decoding crystal phase switching in nanowires*
18:15 – 18:30	**Sebastian Lehmann** Lund University, Sweden *Group V-flow induced zinc blende – wurtzite – zinc blende transition in Au-seeded GaAs nanowires grown by MOVPE*

Wednesday 28th October 2015

Cross-Over Day: NGW+NW

NGW+NW: Photonics

Session Chair: Riccardo Rurali

9:00 – 09:30	**Maria Tchernycheva** Invited IEF-CNRS, France *Nitride nanowire light emitting diodes: from single wire properties to flexible light emitters*
9:30 – 9:45	**Bruno Daudin** Univ. Grenoble Alpes & CEA, INAC-SP2M, France *Molecular beam epitaxy growth of InGaN/GaN nanowire heterostructures*
9:45 – 10:00	**Vilgailé Dagytè** Lund University, Sweden *Characterization of III-V nanowires towards the realisation of intermediate band solar cells*
10:00 – 10:15	**Subhajit Biswas** Tyndall National Institute, University College Cork, Ireland *Bottom-up grown direct bandgap Ge1-xSnx (x> 0.09) nanowires*
10:15 – 10:30	**Diana Huffaker** UCLA, US *Band gap blue-shift induced by Wurtzite crystal phase in InAsSb nanowires grown by selective-area MOCVD*
10:30 – 11:00	**COFFEE BREAK & EXHIBITION (HALL)**

NGW+NW: Transport and Doping

Session Chair: Maria Tchernycheva

11:00 – 11:30	**Shixiong Zhang** Invited Indiana University, US *Controlled growth and enhanced thermoelectric properties of topological crystalline insulator nanowires*
11:30 – 11:45	**Kris A. Bertness** NIST, US *Characterization of Mg Doping in GaN Nanowires with Raman Spectroscopy*

11:45 – 12:00	**Silvia Rubini** IOM-CNR, Italy *Te doping for high electron densities in self-assisted GaAs nanowires*
12:00 – 12:15	**Jessica Boland** University of Oxford, UK *Terahertz Spectroscopy of Modulation Doped GaAs/AlGaAs Core-Shell Nanowires*
12:15 – 12:30	**Kilian Mergenthaler** Lund University, Sweden *Photon Upconversion and Charge Carrier Dynamics in Highly Doped InP Nanowires*

12:30 – 14:30	**LUNCH (included)**

NGW+NW: Hetero & Homostructures, Polytypes

Session Chair: Faustino Martelli

14:30 – 15:00	**Paul C. McIntyre** **Invited** Stanford University *Carrier Dynamics in Ge and Ge-Core/Si(Ge)-Shell Nanowires: Effects of Diameter, Growth and Surface Conditions*
15:00 – 15:15	**Damien Salomon** ESFR, France *Probing Structural Defects and Chemical Heterogeneities in Nanowires with a Multimodal Hard X-Ray Nanoprobe*
15:15 – 15:30	**Qiandong Zhuang** Lancaster University, UK *InAsSb nanowires grown by molecular beam epitaxy for long wavelength infrared optoelectronics*

15:30 – 17:30	**POSTER SESSION B (see page 15) & EXHIBITION (HALL)**

17:30 – 17:45	**Reza Zamani** Lund University, Sweden *Structure Study of III-V heterostructured Nanowires: Polarity and Interfaces*
17:45 – 18:00	**María de la Mata** Institut Català de Nanociència i Nanotecnologia, ICN2, CAT, Spain *III-V Nanowires: an Atomic Resolution Approach*
18:00 – 18:30	**Katsumi Kishino** Invited Sophia University, Japan *Selective area growth of GaN nanocolumns for application to visible nanocolumn emitters*

Thursday 29th October 2015

NW: Quantum Structures and Functionality (I)

Session Chair: Jordi Arbiol

9:00 – 09:30	**Martin Eickhoff** Invited Justus-Liebig-Universität Gießen, Germany *Group III-nitride nanowire hetero- and quantum structures*
9:30 – 09:45	**Nicolas Chauvin** INSA-Lyon, France *Optical anisotropy in single InAs/InP quantum dot and quantum rod nanowires*
9:45 – 10:00	**Davide Cadeddu** University of Basel, Switzerland *A Quantum Fiber-Pigtail*
10:00 – 10:30	**Eva Monroy** Invited CEA, France *Interband and intersubband transitions in GaN/AlN nanowire heterostructures*
10:30 – 11:00	**COFFEE BREAK & EXHIBITION (HALL)**

NW: Quantum Structures and Functionality (II)

Session Chair: Martin Eickhoff

11:00 – 11:30	**Ritesh Agarwal** Invited UPenn, US *Novel classical and quantum photonic devices by manipulating light-matter interactions in low-dimensional systems*
11:30 – 11:45	**Dick Van Dam** TU/e, Netherlands *Directional and polarized nanowire emission governed by waveguide modes*
11:45 – 12:00	**Malin Nilsson** Lund University, Sweden *Single-electron tunnelling in InAs nanowire quantum dots formed by crystal phase engineering*
12:00 – 12:30	**Martin Strassburg** Invited Osram Opto Semiconductors, Germany *High-aspect ratio core-shell InGaN/GaN microrods for future high-efficiency lighting*

12:30 – 14:30	**LUNCH (included)**

NW: Advanced Optoelectronics

Session Chair: Anna Fontcuberta

14:30 – 15:00	**Pierre Corfdir** Invited PDI, Germany *Dielectric confinement of excitons in ultrathin GaN nanowires*
15:00 – 15:15	**Nicklas Anttu** Lund University, Sweden *Nanophotonics in III-V nanowire arrays*
15:15 – 15:30	**Benedikt Mayer** WSI, Germany *Ramsey fringes and ultrafast coherent pulse emission from GaAs-AlGaAs nanowire lasers*

15:30 – 17:30	**POSTER SESSION C (see page 19) & EXHIBITION (HALL)**

17:30 – 18:00	**Martino Poggio** Invited Basel University, Switzerland *Sensing with Nanowires*
18:00 – 18:15	**Jos E.M. Haverkort** TU/e, Netherlands *Digital emission tuning in GaP crystal phase quantum wells*
18:15 – 18:30	**Lars Samuelson** Lund University, Sweden *Nanowire-based Tandem Solar Cells*

Friday 30th October 2015

NW: Transport, Thermoelectronics and Novel Devices

Session Chair: Riccardo Rurali

9:00 – 9:30	**Jose Ordonez** Invited Ecole Centrale Paris, France *Heat Transport in Nanowires Supporting the Propagation of Polaritons and Phonons*
9:30 – 9:45	**Adam Burke** Lund University, Sweden *Nonlinear thermoelectric response due to energy-dependent transport properties of a quantum dot*
9:45 – 10:00	**Xavier Cartoixà Soler** Universitat Autònoma de Barcelona, CAT, Spain *Thermal rectification by design in telescopic Si nanowires*
10:00 – 10:15	**Thomas Sand Jespersen** Niels Bohr Institutet, Denmark *Transport in Epitaxial Semiconductor/superconductor nanowire hybrid quantum dots*
10:15 – 10:30	**Neophytos Neophytou** The University of Warwick, UK *Thermoelectric properties of gated Si nanowires*

10:30 – 11:00	**COFFEE BREAK & EXHIBITION (HALL)**

NW: Nanophotonics and Quantum Physics

Session Chair: Xavier Cartoixà

11:00 – 11:30	**Masaya Notomi** Invited NTT, Japan *Hybrid nanophotonics systems based on sub-wavelength nanowires*
11:30 – 11:45	**Alois Lugstein** TU Wien, Austria *Hot electroluminescence in Si nanowires*

11:45 – 12:00	**Marta de Luca** Sapienza Università di Roma, Italy *Nanowires Are Not So Cool*
12:00 – 12:15	**Jaime Gómez-Rivas** FOM Institute AMOLF, Netherlands *Nanowire Antenna Absorption Probed with Time-Reversed Fourier Microscopy*
12:15 – 12:30	**Martin Leijnse** Lund University, Sweden *Quantum transport in core-shell nanowires*
12:30 – 12:45	**Hao Zhang** TU Delft, Netherlands *Experimental Progress on Majorana Fermions in Semiconductor Nanowire Devices*

12:45 – 13:00	**CLOSURE**

NANOWIRES

BARCELONA 2015

POSTER SESSIONS

POSTER SESSION – A

Tuesday 27th October 2015 **Nanowire Growth Workshop**

15:30 – 17:30	POSTER SESSION A NGW
NGW1	**Samik Mukherjee** Polytechnique Montréal, Canada *Dynamics of the Nanowire VLS Growth Unravelled by Isotope Tracing*
NGW2	**Tomáš Pejchal** Brno University of Technology, Czech Republic *The Role of Hydrogen in Ge Nanowire Growth*
NGW3	**Mariam Fakhfakh** Institut d'Electronique Fondamentale, CNRS-UMR, France *Characterization of Ge nanowires under Mn implantation*
NGW4	**Jessica Doherty** University College Cork, Ireland *Induction of Twinning and Polytypes in Diameter Controlled Germanium Nanowires*
NGW5	**Nicolas Hibst** Ulm University, Germany *Exploring the Growth Regimes of Platinum Catalyzed Silicon Nanowire Growth*
NGW6	**Jessica Bolinsson** University of Copenhagen, Denmark *Silver as a catalyst for growth of GaAs nanowires*
NGW7	**Rong Su** Lund University, Sweden *Effect of V-III ratio on low-temperature growth Sn-seeded GaAs nanowire*
NGW8	**Zhenning Dong** Clermont Université, Clermont-Ferrand, France *Ga-Catalyst GaAs Nanowires grown on Silicon by HVPE*
NGW9	**Teemu Hakkarainen** Tampere University of Technology, Finland *Self-induced growth of GaAs nanowires on lithography-free Si/SiO_x patterns*
NGW10	**Julian Jakob** Karlsruhe Institute of Technology, Germany *Tailoring of GaAs NW for in-situ X-ray investigations using a portable MBE*

NGW11	**Seyed Mohammad Mostafavi Kashani** University of Siegen & Karlsruhe Institute of Technology, Germany *Thermal annealing of GaAs nanowires studied by in-situ time-resolved x-ray diffraction*
NGW12	**Alexander A. Koriakin** St. Petersburg Academic University and ITMO University, Russia *Modeling of GaAs nanowire formation via selective-area MOCVD*
NGW13	**Jurij Grecenkov** St. Petersburg Academic University, Russia *Modelling of the growth Au-catalysed of InGaAs nanowires: interplay of group III elements and the role of group V*
NGW14	**Nikolai V. Sibirev** St. Petersburg Academic University, Russia *Step propagation and the shape of nanowires*
NGW15	**Masoomeh Ghasemi** Lund University, Sweden *Studying the phase stability of the nanoscale InSb systems*
NGW16	**Marcus Tornberg** Lund University, Sweden *Homoepitaxial growth of Sn-seeded antimonide-based nanowires by MOVPE*
NGW17	**Ezekiel A. Anyebe** Lancaster University, United Kingdom *Arsenic flux - induced suppression of lateral growth in InAsSb nanowires grown on Graphite*
NGW18	**Hayfaa Alradhi** Lancaster University, United Kingdom *Realization of InAs/AlSb core-shell NWs grown by MBE*
NGW19	**Heidi Potts** EPFL, Switzerland *Growth and characterization of twin-free $InAs_{1-x}Sb_x$ nanowires*
NGW20	**Thomas Kanne** University of Copenhagen, Denmark *$InAs_{1-x}Sb_x$ / Al core-shell nanowire epitaxy*
NGW21	**Saša Gazibegović** TU Delft and TU Eindhoven, Netherlands *Epitaxial Growth of Aluminum on InSb Nanowires*
NGW22	**Jung-Hyun Kang** Weizmann Inst., Israel *In-situ MBE Al Coated Thin InAs Nanowires and Merged Intersections*

NGW23	**Caroline Lindberg** University of Copenhagen, Denmark *Exploring growth of silver catalysed InAs nanowires*
NGW24	**Daniele Ercolani** Scuola Normale Superiore and Istituto di Nanoscienze-CNR, Pisa, Italy *Nucleation mechanisms and growth kinetics of Catalyst-free InAs nanowires grown on Si (111)*
NGW25	**Mitchell T. Robson** McMaster University, Hamilton, Canada *Growth modes of InAs nanowires on Si(111) substrates*
NGW26	**Nataliya Shwartz** Institute of Semiconductor Physics, Novosibirsk, Russia *Simulation of self-catalyzed InAs and GaAs nanowire growth*
NGW27	**Jan Schmidtbauer** Lund University, Sweden, and Leibniz Institute for Crystal Growth, Berlin, Germany *Mechanisms leading to broadened length distributions of nanowires*
NGW28	**Lucia Sorba** Scuola Normale Superiore and Istituto di Nanoscienze-CNR, Pisa, Italy *Diameter distribution of InAs nanowires grown by Au-assisted methods*
NGW29	**Guoqiang Zhang** NTT Basic Research Laboratories, Japan *Atomically-abrupt interface by stacking fault engineering*
NGW30	**Marta Sobanska** Polish Academy of Sciences, Warsaw, Poland *Kinetics of spontaneous nucleation and PAMBE growth of GaN nanowires on amorphous Al_xO_y studied by RHEED*
NGW31	**Vishnuvarthan Kumaresan** CNRS - Laboratoire de Photonique et de Nanostructures, France *New Templates for Self-induced Growth of Vertical GaN Nanowires*
NGW32	**Saskia Weiszer** WSI, TU München, Germany *MBE growth and characterization of InGaN nanowires on Si (111)*
NGW33	**Tandra Ghoshal** University College Cork & CRANN/AMBER, Trinity College Dublin, Ireland *Large scale in-plane Si nanowire arrays on Si substrate: An insitu hard mask block copolymer approach*
NGW34	**Jelena Vukajlović Pleština** EPFL, Switzerland *Modification of the surface properties for achieving high yield GaAs nanowire arrays on silicon*
NGW35	**Siew Li Tan** CEA/CNRS/UJF Joint Team "Nanophysics and Semiconductors", Grenoble, France *Selectivity and yield improvement in selectively grown GaAs nanowires on Si*

NGW36	**Danial Bahrami** Universität Siegen, Germany *Focused Ion Beam Pre-Patterning of Si substrates for the growth of GaAs nanowires*
NGW37	**Aiyeshah Alhodaib** Lancaster University, UK *Catalyst-free selective area MBE of semiconductors nanowires on a Si pattern substrate*
NGW38	**Joona-Pekko Kakko** Aalto University, Finland *Fabrication of Dual-Type Nanowire Arrays*
NGW39	**Gozde Tutuncuoglu** EPFL, Switzerland *Heterostructures based on GaAs nanoscale membranes*
NGW40	**Kaddour Lekhal** Nagoya University, Japan *Compatibility of hydride vapor phase epitaxy process with synthesis of horizontal and vertical GaN nanowires*
NGW41	**Maryam Khalilian** Lund University, Sweden *Control of dislocations in GaN nanowires*
NGW42	**Blandine Alloing** CRHEA-CNRS, Valbonne, France *Dislocation-filtering and polarity in the selective area growth of GaN nanowires by continuous-flow MOVPE*

POSTER SESSION – B

Wednesday 28th October 2015 **Cross-Over Day: NGW+NW**

15:30 – 17:30	POSTER SESSION B NGW-NW (Cross-Over Day)
NGWxNW1	**Jian Tang** LPICM-CNRS, France *Composition and crystallinity characterization of tin-catalyzed $Si_{1-x}Ge_x$ nanowires grown by plasma assisted vapor-liquid-solid*
NGWxNW2	**Christopher Davies** University of Oxford, UK *High Ensemble Uniformity and Low Disorders in Quantum Well Tube Nanowires Probed by Photoluminescence Spectroscopy*
NGWxNW3	**Michele Amato** IEF, France *Shell-Thickness Controlled Semiconductor-Metal Transition in Si-SiC Core-Shell Nanowires*
NGWxNW4	**Doriane Djomani** Université Paris-Sud, France *Strain-induced phase transformation in Ge nanowires*
NGWxNW5	**Luca Boarino** INRiM, Italy *Ordered Silicon Nanowires by Metal Assisted Chemical Etching*
NGWXNW6	**Isabel Alonso** ICMAB-CSIC, CAT, Spain *Micro-Raman spectroscopy and imaging of epitaxial SiGe nanowires grown on Si(001)*
NGWxNW7	**Rianne Plantenga** TU Eindhoven, Netherlands *Hexagonal GaP-Si-SiGe core-multishell nanowires studied by Atom Probe Tomography*
NGWxNW8	**Valentina Zannier** Scuola Normale Superiore and Istituto di Nanoscienze-CNR, Pisa, Italy *Optical properties of single wurtzite/zinc-blende ZnSe nanowires grown at low temperature*
NGWxNW9	**Arman Davtyan** University of Siegen, Germany *Randomly distributed phase domains in single GaAs NWs*
NGWxNW10	**Zbigniew R. Zytkiewicz** Polish Academy of Sciences, Warsaw, Poland *Influence of growth conditions on optical properties of GaN nanowires grown by PAMBE on amorphous Al_xO_y*

NGWxNW11	**Bruno Daudin** Univ. Grenoble Alpes, CEA, INAC-SP2M, and CNRS, France *High Si incorporation in MBE-grown GaN nanowires*
NGWxNW12	**Matthew D. Brubaker** NIST, US *Selective area growth and surface recombination velocity measurements in N-polar gallium nitride nanowire arrays*
NGWxNW13	**Martin Hetzl** WSI, TU München, Germany *Growth and electrical transport properties of GaN nanowire/diamond heterojunctions*
NGWxNW14	**Matthias Belloeil** CEA Grenoble, France *Growth, structural and optical characterizations of AlGaN/GaN nanowire heterostructures*
NGWxNW15	**Jonas Lähnemann** INAC CEA Grenoble, France *UV photodetector based on single GaN/AlN nanowire heterostructures*
NGWxNW16	**Yuta Konno** Sophia University, Japan *InGaN/GaN p-i-n nanocolumns grown on SiO_2/Si (100) substrates employing AlN/graphene*
NGWxNW17	**Claudia Speich** Univ. Duisburg-Essen, Germany *MOVPE grown axial n-GaN/p-GaAs nanowires*
NGWxNW18	**Daria Beznasyuk** Institut Néel - CNRS, France *Towards axial Si/GaAs nanowire heterostructures*
NGWxNW19	**Suzanne Lancaster** TU Wien, Austria *Zn dopant incorporation via contact annealing of GaAs nanowires*
NGWxNW20	**Amaury Mavel** Université de Lyon and INSA Lyon, France *Quantum confinement effect in InAs/InP quantum dot nanowires (QD-NWs) grown on silicon-*
NGWxNW21	**Jonathan Becker** WSI, TU München, Germany *Correlation of microstructure and electrical transport characteristics in InAs Nanowires*
NGWxNW22	**Alessandro Cavalli** TU Eindhoven, Netherlands *Growth of Selective-Area MOVPE In(Ga)P Nanowires*

NGWxNW23	**Diana Huffaker** UCLA, US *Dead-space effect in InGaAs nanopillar avalanche photodetectors*
NGWxNW24	**Julian Treu** WSI, TU München, Germany *Widely tunable InGaAs nanowire heterostructures and devices*
NGWxNW25	**Maximilian Speckbacher** WSI, TU München, Germany *Optical investigation of surface Fermi level-pinning in high periodicity InGaAs nanowire arrays*
NGWxNW26	**Xulu Zeng** Lund University, Sweden *Growth and doping evaluation of p-type GaInP nanowires*
NGWxNW27	**Vishal Jain** Lund University, Sweden *Design and realization of InP/InAsP nanowire-based avalanche photodetectors*
NGWxNW28	**Luca Gagliano** TU Eindhoven, Netherlands *Pure Wurtzite GaP/InGaP core-multishell quantum well nanowires for Solid State Lighting*
NGWxNW29	**Johannes Greil** TU Eindhoven, Netherlands *Effects of uniaxial strain on the PL emission spectrum of WZ GaP nanowires*
NGWxNW30	**Rawa Tanta** NBI, Copenhagen Univ., Denmark *Surface-dependent oxidation of branched InAs nanowires*
NGWxNW31	**Sebastien Plissard** CNRS, LAAS, and Univ de Toulouse, France *Formation and optical properties of GaAsSb nanowire networks*
NGWxNW32	**Junghwan Huh** Norwegian University of Science and Technology, Trondheim, Norway *Photocurrent Mapping of Single GaAsSb Nanowire Diodes*
NGWxNW33	**Veer Dhaka** Aalto University, Finland *Protective capping and surface passivation of III-V nanowires by ALD*
NGWxNW34	**Tuomas Haggrén** Aalto University, Finland *Efficient and simple surface passivation method for GaAs nanowires*
NGWxNW35	**Mukesh Kumar** Indian Institute of Technology Delhi, India *Coaxial GaN/Ga_2O_3 heterostructure nanowires formed via ammonification process*

NGWxNW36	**Linus Krieg** TU Braunschweig, Germany *Conformal growth of ultra-thin p-conductive polymer shells on n-type semiconductor nanowires by oxidative chemical vapour deposition*
NGWxNW37	**Sonia Conesa-Boj** TU Delft, Netherlands *Towards defect-free hexagonal Si from suppression of crack defect formation*
NGWxNW38	**Aloyzas Šiušys** Polish Academy of Sciences, Warsaw, Poland *Magnetic and structural properties of MBE grown wurtzite (Ga,Mn)As shells in a radial quantum well nanowire heterostructures*
NGWxNW39	**Ali Hassan** Univ. of Siegen, Germany *Elastic strain relaxation in GaAs/InGaAs/GaAs core-shell NW heterostructures grown by MBE on Si (111)*
NGWxNW40	**Jessica Boland** Oxford Univ., UK *High Ensemble Uniformity and Low Disorders in Quantum Well Tube Nanowires Probed by Photoluminescence Spectroscopy*
NGWxNW41	**Llorenç Servera Serapio** EUSS, CAT, Spain *Process of manufacturing of a carbonaceous material for supercapacitors applications*
NGWxNW42	**Oscar Kennedy** University College London, UK *Surface luminescence in ZnO nanowires*

POSTER SESSION – C

Thursday 29th October 2015 **Nanowires Workshop**

15:30 – 17:30	POSTER SESSION C NW
NW1	**Thomas Stettner** WSI, TU München, Germany *Monolithically integrated core-shell GaAs-AlGaAs NW lasers on Si*
NW2	**Jonas Vogel** Siegen Univ., Germany *Investigation of single objects in GaAs Nanowire ensemble measurements by x-ray diffraction*
NW3	**Julia Winnerl** WSI, TU München, Germany *0D quantum emitters in ultrathin GaAs nanowires*
NW4	**Lorenzo di Mario** IMM-CNR, Italy *Study of the Schottky barrier on single GaAs nanowires by X-ray PhotoEmission Electron Microscopy*
NW5	**Luca Francaviglia** EPFL, Switzerland *Shell quantum dots in core-shell GaAs-AlGaAs nanowires studied by photoluminescence and cathodoluminescence*
NW6	**Dmitry Mikulik** EPFL, Switzerland *Towards flexible GaAs nanowire-based solar cells*
NW7	**Eleonora Frau** EPFL, Switzerland *Photocatalytic water splitting with GaAs nanowires*
NW8	**Patrick Zellekens** Forschungszentrum Jülich, Germany *Angle dependent magnetoconductance oscillations and Hall measurements in GaAs/InAs Core/Shell Nanowires*
NW9	**Xiaomo Xu** WSI, TU München, Germany *Selective-area epitaxial grown In1-xGaxAs nanowires using novel UV-cured nano-imprint lithography*
NW10	**Floris Braakman** Basel Univ., Switzerland *Nonlinear mechanical mode coupling and quantum dots in grown GaAs nanowire*

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